

Figure 1
Prior Art

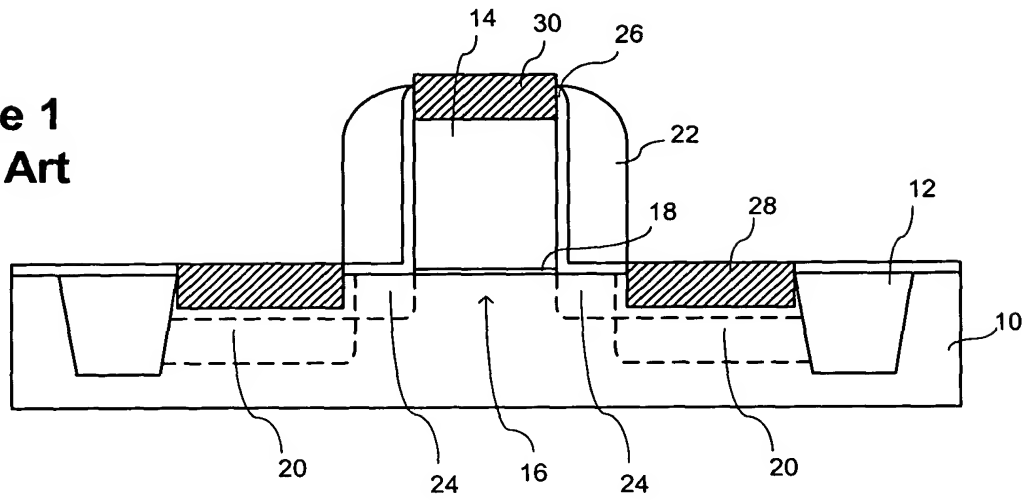


Figure 2
Prior Art

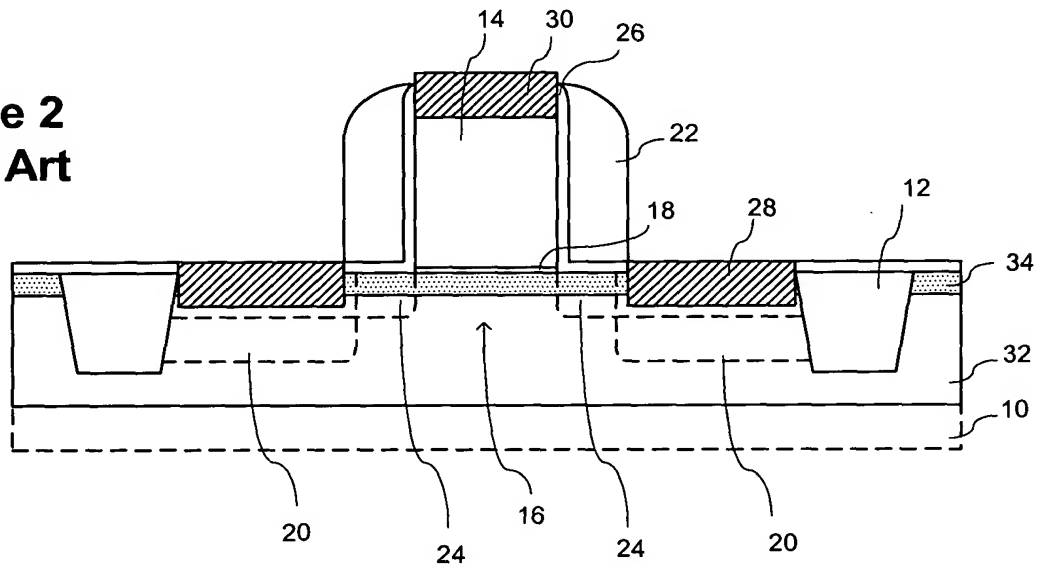
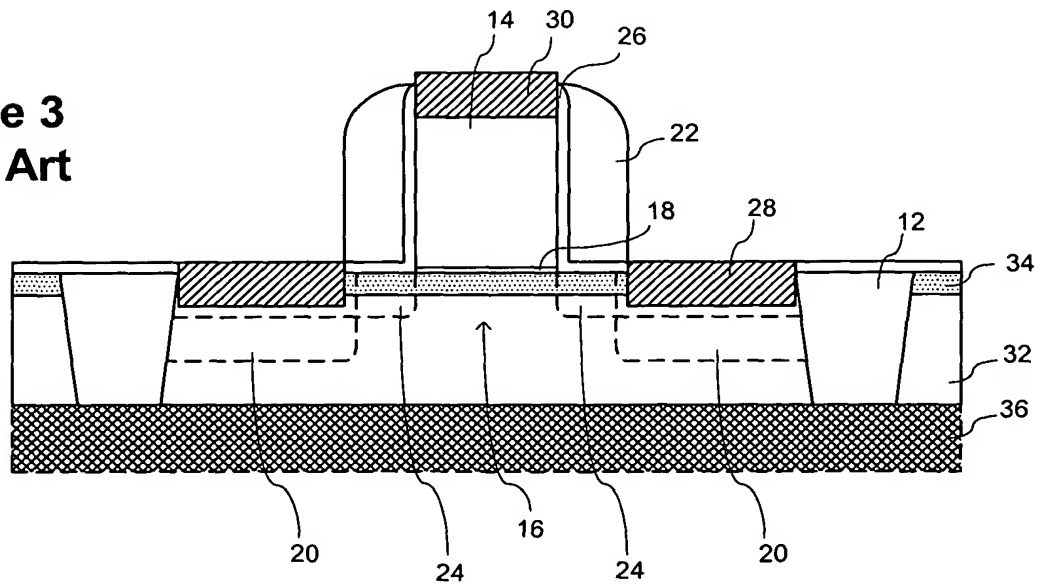


Figure 3
Prior Art



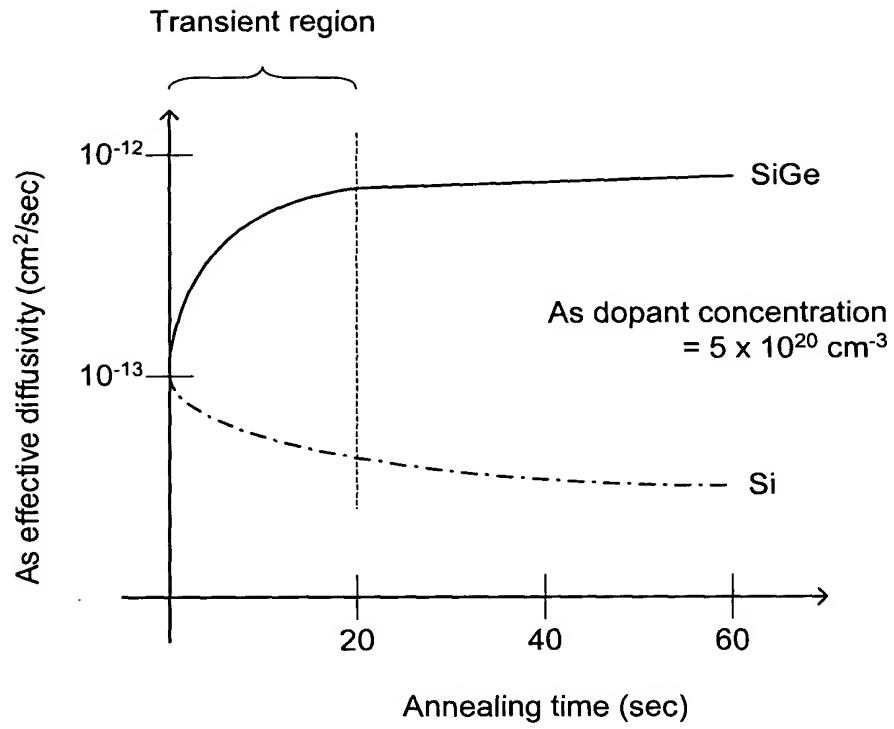


Figure 4

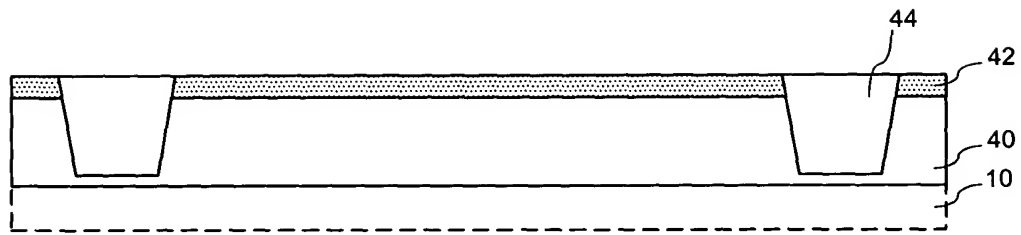


Figure 5a

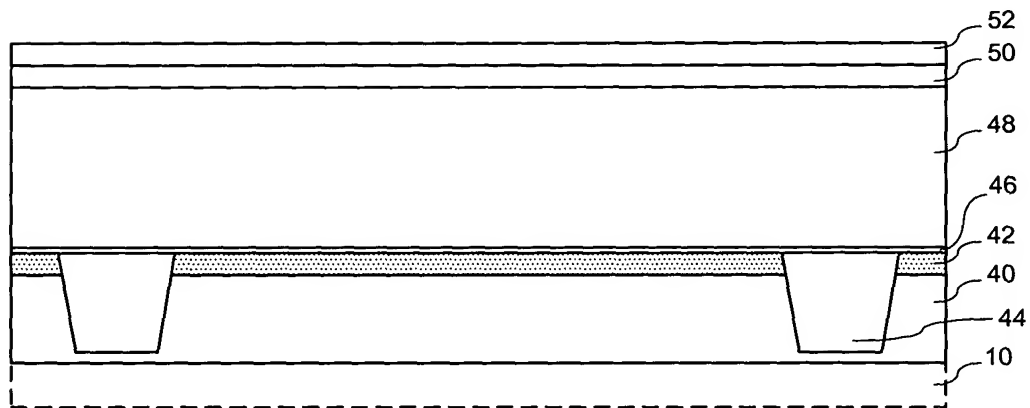


Figure 5b

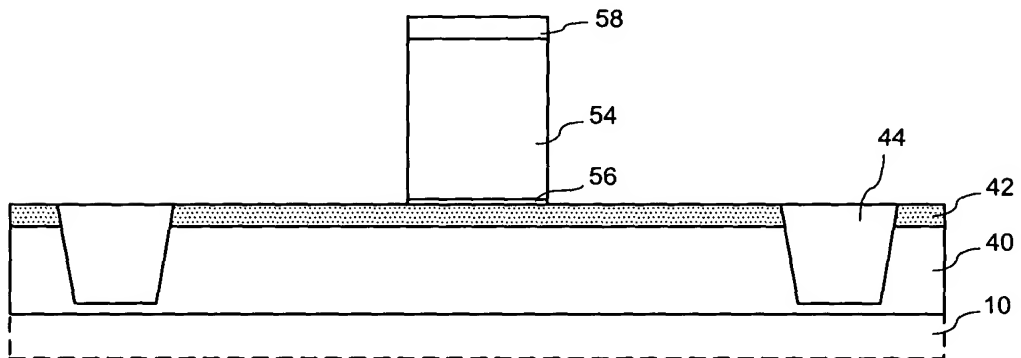


Figure 5c

This cross-sectional view shows a semiconductor device with a central raised portion. The device consists of a substrate (10) with a top layer (40) and a thin layer (42) on top. A central raised portion (54) is formed on the top layer, with a top surface (58) and side walls (60). The raised portion is connected to the substrate by a base layer (56). The base layer is formed by a series of steps (44) and is shown with a dashed line (62) indicating its profile. The substrate (10) has a dashed line (62) indicating its bottom profile.

Figure 5f

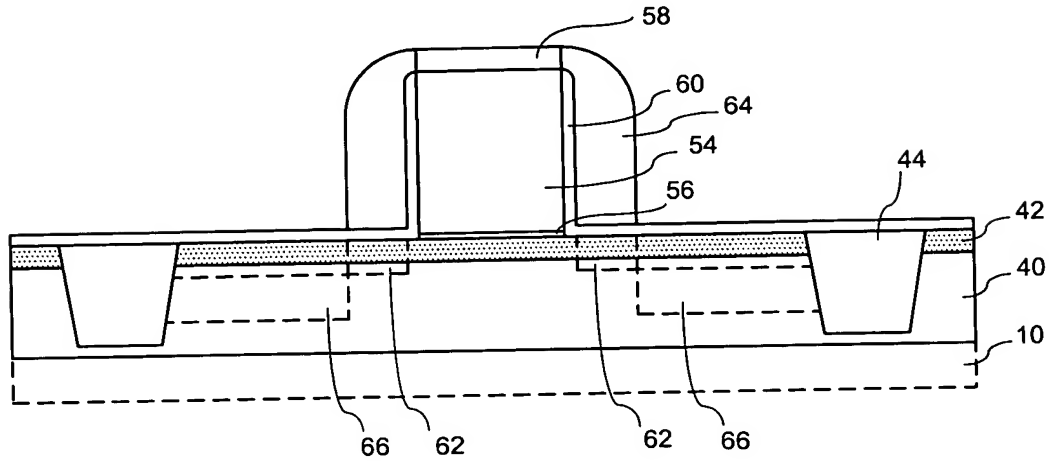


Figure 5g

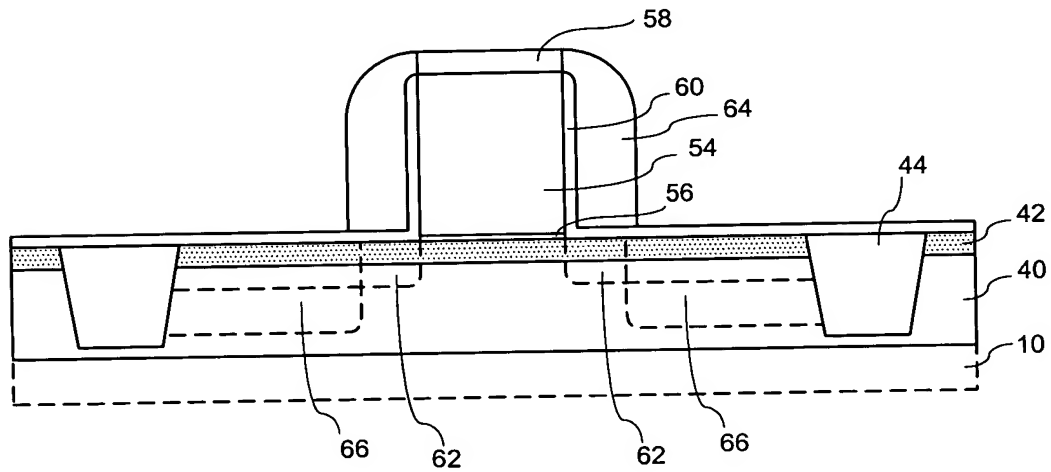


Figure 5h

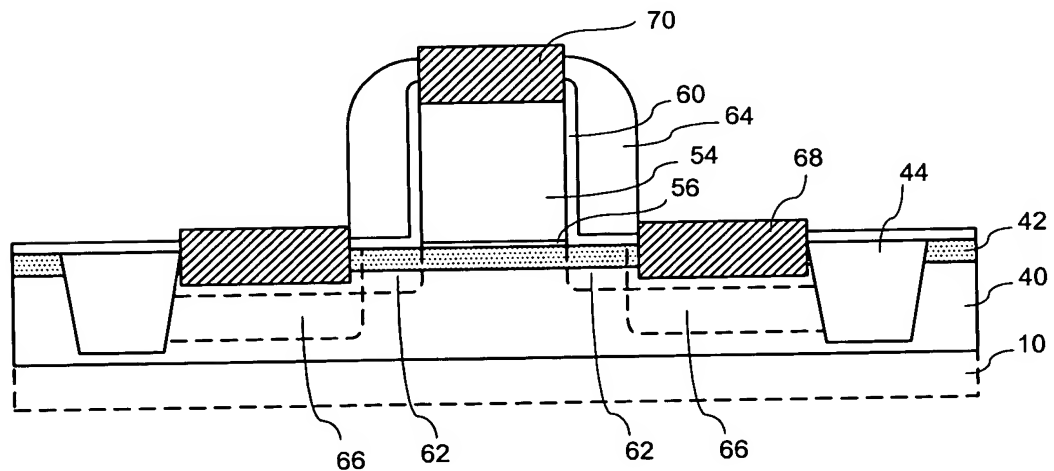


Figure 5i

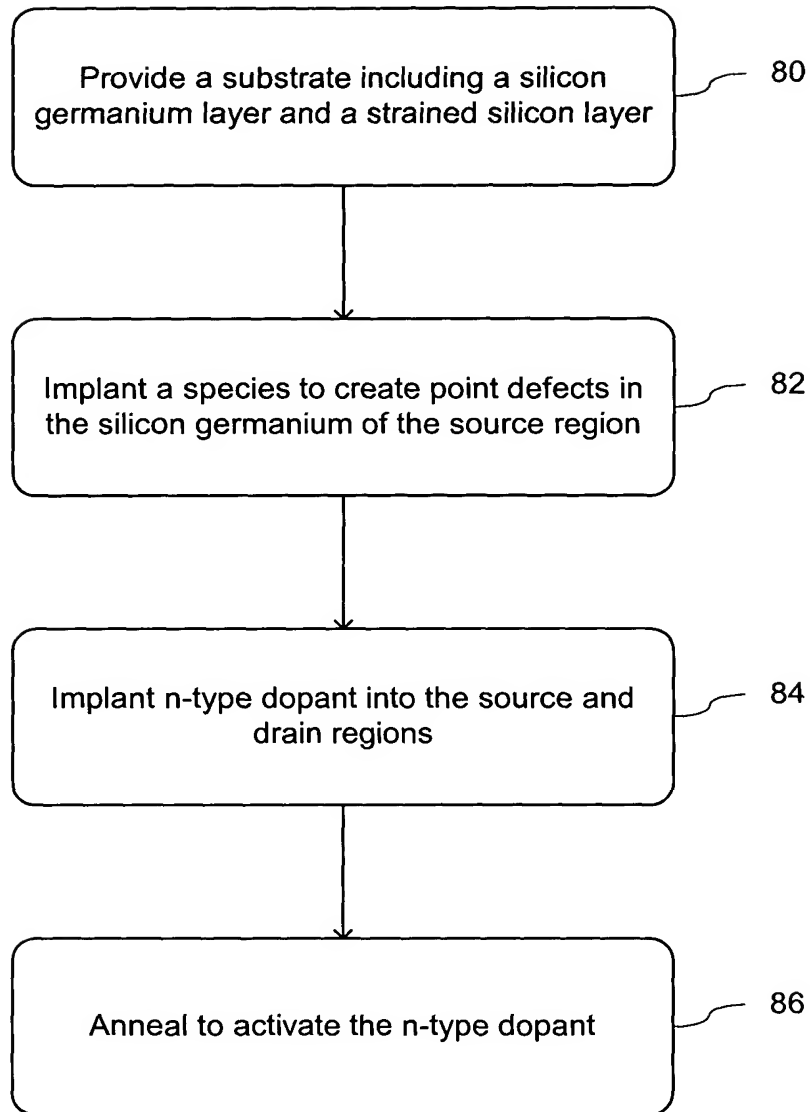


Figure 6